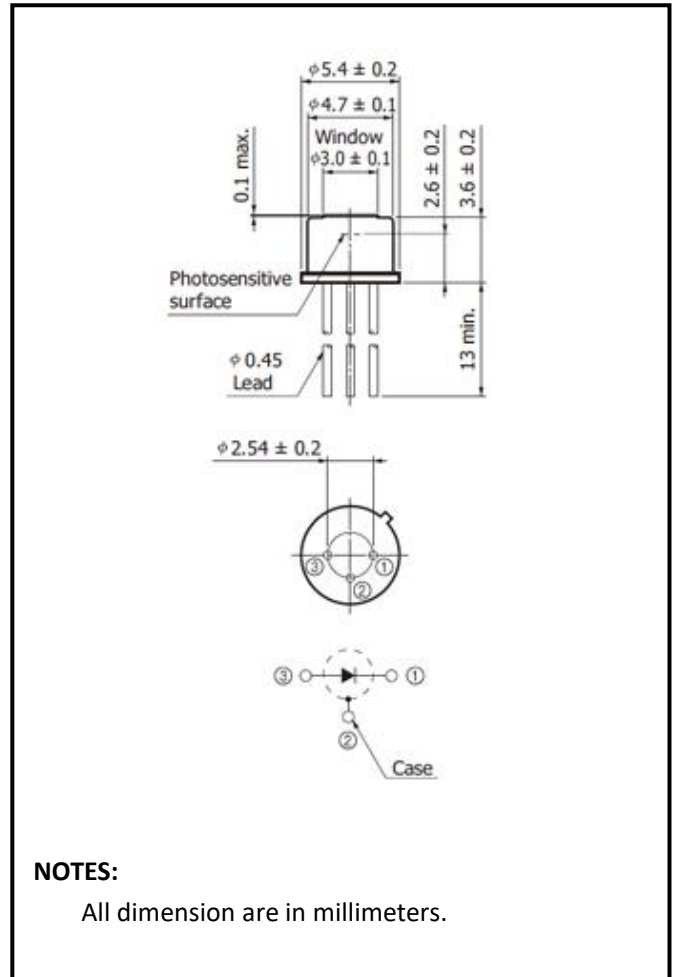


## InGaAs PIN Photodiode

### IGA1000



## Description

OTRON SENSOR IGA1000 is a type of active area size of 1mm diameter active area IR sensitive detectors which exhibit excellent responsivity from 1000nm to 1680nm, allowing high sensitivity to weak signals.

These large active area devices are ideal for use in infrared instrumentation and monitoring applications.

We can also custom type according to customer chip size or Package style enquiry.

## Features

- \* Low voltage operation
- \* Isolated type are also available
- \* Large Active Area Diameter
- \* Spectral Range 800nm to 1700nm

## General Ratings

- \* Type InGaAs Photodiode
- \* High linearity
- \* Low cost
- \* Low dark current

## Applications

- \* Optical Instrumentation
- \* NIR Sensing
- \* Laser Power Measurement
- \* Power meters

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice

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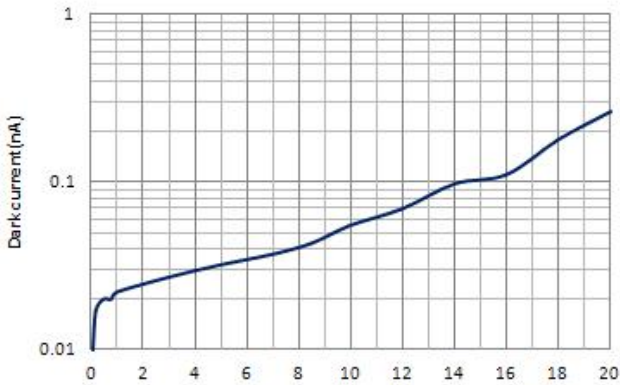


## Absolute Maximum Ratings (Ta=25°C)

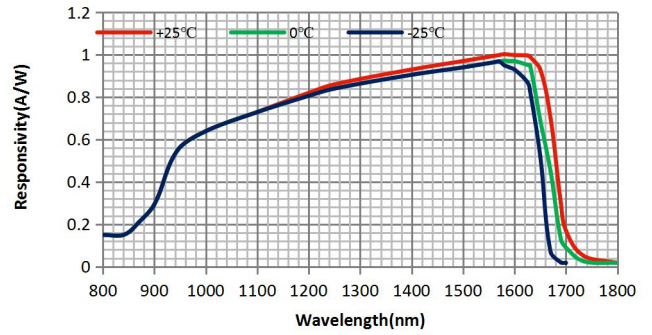
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	s	1290×1290×175				um
Active area	A	φ 1000				um
Forward current	I <sub>F</sub>	10				mA
Reverse current	I <sub>R</sub>	10				mA
Dark current	I <sub>D</sub>	V <sub>R</sub> =0V		10		pA
		V <sub>R</sub> =5V		32		
Rise time	t <sub>R</sub>	V <sub>R</sub> =5V;R <sub>L</sub> =50Ω, f=1MHz		3	5	ns
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =1mA			0.6	V
Reverse breakdown voltage	V <sub>(BR)R</sub>	I <sub>R</sub> =10μA Ev=0lx		40		V
Junction Capacitance	C <sub>J</sub>	V <sub>R</sub> =0V f=1MHz		14		uF
		V <sub>R</sub> =5V f=1MHz		2.67		uF
Photo sensitivity	S <sub>R</sub>	1310nm		0.95	0.97	A/W
		1550nm		0.98	1.10	
Spectral Application Range	λ <sub>range</sub>			1000	1680	nm
Spectral Response-Peak	λ <sub>p</sub>			1600		nm
Shunt resistance	R <sub>sh</sub>	V <sub>R</sub> =10mV		75		MΩ
Saturation power	L	V <sub>R</sub> =0V;λ=1.55μm		1	1.6	mW
		V <sub>R</sub> =2V;λ=1.55μm		2	5.3	
		V <sub>R</sub> =5V;λ=1.55μm		6	12.1	
Angular Resp 50% Resp Pt	θ <sub>1/2</sub>			±55		Degrees
Noise Equivalent Power	NEP	V <sub>R</sub> =5V λ=1550nm		8.16×10 <sup>-13</sup>		W/Hz <sup>1/2</sup>
Specific Detectivity	D*	V <sub>R</sub> =5V λ=1550nm		2.17×10 <sup>12</sup>		cm(Hz/W) <sup>1/2</sup>

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## ■ Dark current vs. reverse voltage

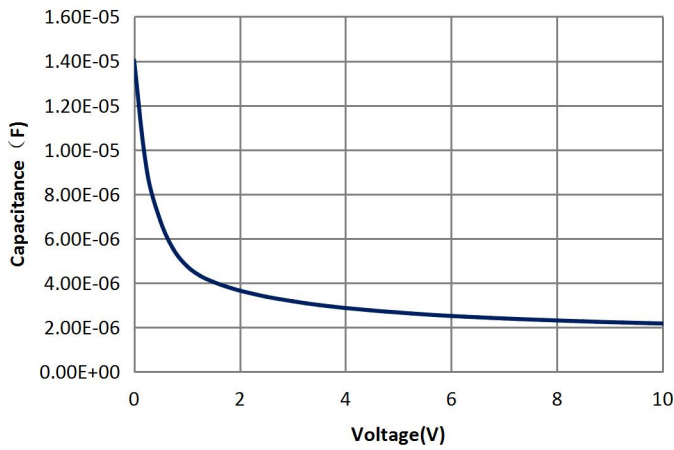


## ■ Spectral response



## ■ Relative Junction Capacitance

### VS. Voltage



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